# Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

## **High-Performance Silicon-Gate CMOS**

The MC74HC541A is identical in pinout to the LS541. The device inputs are compatible with Standard CMOS outputs. External pull-up resistors make them compatible with LSTTL outputs.

The HC541A is an octal noninverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC541A is similar in function to the HC540A, which has inverting outputs.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- Pb-Free Packages are Available\*



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#### MARKING DIAGRAMS



PDIP-20 N SUFFIX CASE 738

20 AAAAAAAAAAA MC74HC541AN O AWLYYWWG

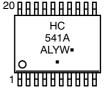


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package
 Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

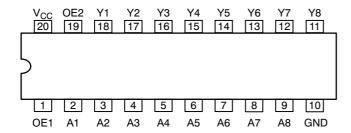


Figure 1. Pinout: 20-Lead Packages (Top View)

#### **FUNCTION TABLE**

	Inputs	Output Y		
OE1	DE1 OE2 A		Output 1	
L	L	L	L	
L	L	Н	Н	
Н	Х	Х	Z	
Х	Н	Х	Z	

X = Don't Care Z = High Impedance

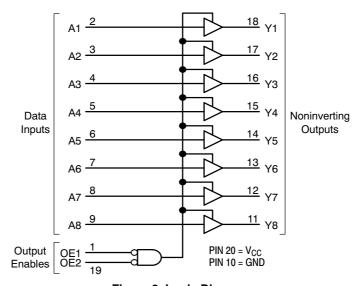


Figure 2. Logic Diagram

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC541AN	PDIP-20	18 Units / Rail
MC74HC541ANG	PDIP-20 (Pb-Free)	18 Units / Rail
MC74HC541ADW	SOIC-20 WIDE	38 Units / Rail
MC74HC541ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC541ADWR2	SOIC-20 WIDE	1000 Tape & Reel
MC74HC541ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC541ADT	TSSOP-20*	75 Units / Rail
MC74HC541ADTG	TSSOP-20*	75 Units / Rail
MC74HC541ADTR2	TSSOP-20*	2500 Tape & Reel
MC74HC541ADTR2G	TSSOP-20*	2500 Tape & Reel
MC74HC541AF	SOEIAJ-20	40 Units / Rail
MC74HC541AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74HC541AFEL	SOEIAJ-20	2000 Tape & Reel
MC74HC541AFELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb-Free.

#### **MAXIMUM RATINGS**

Symbol	F	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5  to  +7.0	V
VI	DC Input Voltage		$-0.5 \le V_{\parallel} \le +0.5$	V
Vo	DC Output Voltage (Note 1)		$-0.5 \le V_0 \le +0.5$	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
I <sub>OK</sub>	DC Output Diode Current		±35	mA
Io	DC Output Sink Current		±35	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±75	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±75	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for	or 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance	PDIP SOIC TSSOP	67 96 128	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% - 35%	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 4000 > 300 > 1000	V
I <sub>Latchup</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I<sub>O</sub> absolute maximum rating must be observed.

- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.
- 6. For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 3)	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	0 0 0	1000 500 400	ns

7. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

#### DC CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit		mit	
Symbol	Parameter	Condition	V <sub>CC</sub> V	−55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>OUT</sub> = 0.1 V  I <sub>OUT</sub>   ≤ 20 μA	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{OUT} = V_{CC} - 0.1 \text{ V}$ $ I_{OUT}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	٧
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{IN} = V_{IL}$ $ I_{OUT}  \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	٧
		$ \begin{aligned} V_{IN} = V_{IL} & &  I_{OUT}  \leq 3.6 \text{ mA} \\ &  I_{OUT}  \leq 6.0 \text{ mA} \\ &  I_{OUT}  \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT}  \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
			3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ
l <sub>OZ</sub>	Maximum 3-State Leakage Current	Output in High Impedance State $V_{IN} = V_{IL}$ or $V_{IH}$ $V_{OUT} = V_{CC}$ or GND	6.0	± 0.5	±5.0	±10.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>IN</sub> = V <sub>CC</sub> or GND I <sub>OUT</sub> = 0 μA	6.0	4	40	160	μΑ

<sup>8.</sup> Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **AC CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

			Gu	Guaranteed Limit		
Symbol	Parameter	V <sub>CC</sub> V	−55 to 25°C	≤85°C	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 4 and 6)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 3 and 5)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C <sub>IN</sub>	Maximum Input Capacitance		10	10	10	pF
C <sub>OUT</sub>	Maximum 3-State Output Capacitance (High Impedance State Output)		15	15	15	pF

<sup>9.</sup> For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer) (Note 10)	35	pF

<sup>10.</sup>Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

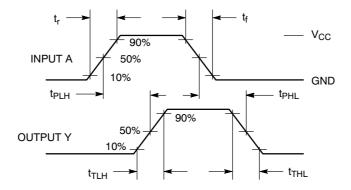


Figure 3. Switching Waveform

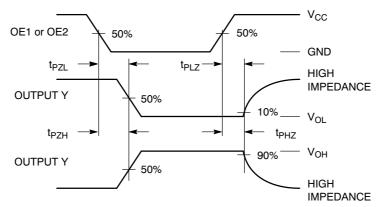
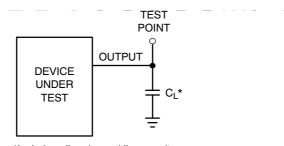
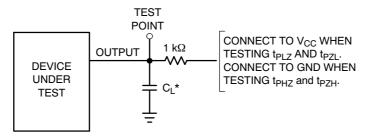


Figure 4. Switching Waveform



\*Includes all probe and jig capacitance

Figure 5. Test Circuit



\*Includes all probe and jig capacitance

Figure 6. Test Circuit

#### PIN DESCRIPTIONS

#### **INPUTS**

#### A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in non-inverted form on the corresponding Y outputs, when the outputs are enabled.

#### **CONTROLS**

#### OE1, OE2 (PINS 1, 19)

Output enables (active-low). When a low voltage is applied to both of these pins, the outputs are enabled and the

device functions as an non-inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

#### **OUTPUTS**

# Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either non-inverting outputs or high-impedance outputs.

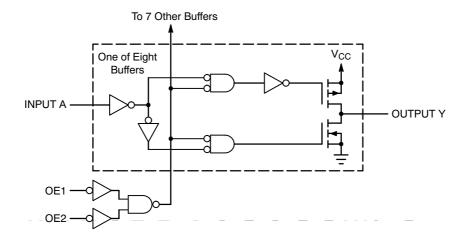
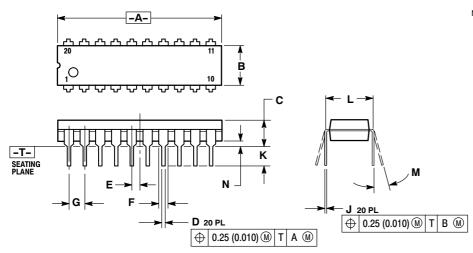


Figure 7. Logic Detail

#### PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E

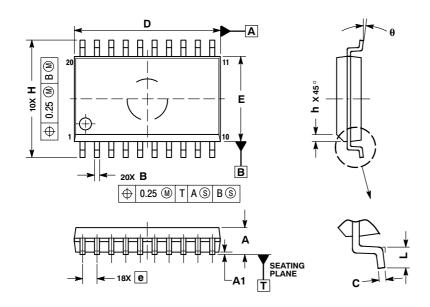


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
C	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
Е	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

#### SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



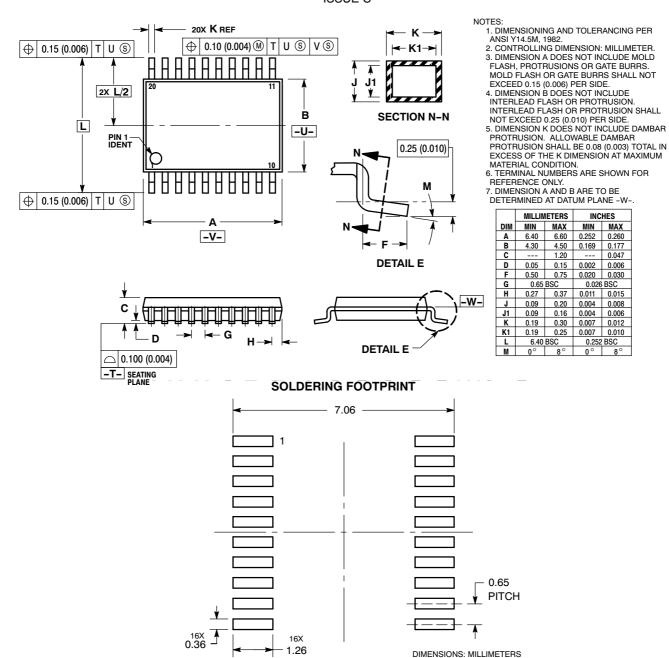
#### NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- PHOTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION, ALLOWABLE PROTRUSION
  SHALL BE 0.13 TOTAL IN EXCESS OF B
  DIMENSION AT MAXIMUM MATERIAL
  CONDITION.

MILLIMETERS DIM MIN MAX Α 2.35 2.65 **A1** 0.10 0.25 B C 0.35 0.49 0.23 **D** 12.65 12.95 7.40 7.60 1.27 BSC H 10.05 10.55 h 0.25 0.75 0.50 0.90 0° 7°

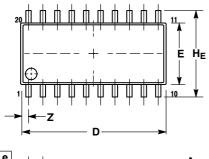
#### PACKAGE DIMENSIONS

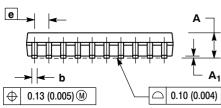
#### TSSOP-20 DT SUFFIX CASE 948E-02 ISSUE C

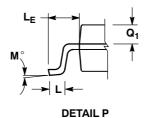


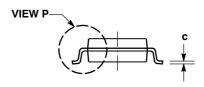
#### PACKAGE DIMENSIONS

SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE A** 









#### NOTES:

- 1. DIMENO. Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.81		0.032

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